



PATENT
Attorney Docket No. ASC-022CPC1

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT: Wu et al.
SERIAL NO.: 10/603,852 GROUP NO.: 2811
FILING DATE: June 25, 2003 EXAMINER: Douglas Owens
TITLE: ETCH STOP LAYER SYSTEM

Mail Stop ISSUE FEE
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Alexandria, VA 22313-1450

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The references listed on the enclosed Form PTO/SB/08 are submitted solely in compliance with the duty of candor. It is understood that this Information Disclosure Statement does not fall within the provisions of 37 C.F.R. §1.97. Copies of cited non-patent literature numbered C176-C196 are enclosed.

It is respectfully requested that the references listed on the attached Form PTO/SB/08, and other information contained herein, be made of record in this application.

Respectfully submitted,

Date: April 3, 2007
Reg. No. 44,381

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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

Sheet	1	of	2	Attorney Docket Number	ASC-022CPC1
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Complete if Known

Application Number	10/603,852
Filing Date	June 25, 2003
First Named Inventor	Eugene A. Fitzgerald
Art Unit	2811
Examiner Name	D. W. Owens
Attorney Docket Number	ASC-022CPC1

U.S. PATENT DOCUMENTS

Examiner Initials	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
	A295	US-20020167048-A1	11-14-2002	Tweet et al.	
	A296	US-20030027381-A1	02-06-2003	Buynoski et al.	
	A297	US-20030077867-A1	04-24-2003	Fitzgerald	
	A298	US-20030141548-A1	07-31-2003	Anderson et al.	
	A299	US-20040007715-A1	08-30-2005	Webb et al.	
	A300	US-20040161947-A1	08-19-2004	Fitzgerald	
	A301	US-20040173790-A1	09-09-2004	Yeo et al.	
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	A307	US-6,534,380	03-18-2003	Yamauchi et al.	
	A308	US-6,621,131-A1	09-16-2003	Murthy et al.	
	A309	US-7,091,095-A1	08-15-2006	Chu	

FOREIGN PATENT DOCUMENTS

Examiner Initials	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. CITE NO.: Those application(s) which are marked with a single asterisk (*) next to the Cite No. are not supplied (under 37 CFR 1.98(a)(2)(iii)) because that application was filed after June 30, 2003 or is available in the IFW. ¹ Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
	C176	Al-Bayati et al., "Exploring the limits of pre-amorphization implants on controlling channeling and diffusion of low energy B implants and ultra shallow junction formation," 2000 Conf. on Ion Implantation Technology, pp. 54-57.	
	C177	Andrieu et al., "Co-integrated Dual Strained Channels on Fully Depleted sSDOI CMOSFETs with HfO ₂ /TiN Gate Stack down to 15 nm Gate Length," 2005 IEEE Int'l SOI Conf. Proc., pp. 223-224.	
	C178	Examination Report for European Patent Application No. 01 973 651.1, dated Sept. 7, 2005, 4 pages.	
	C179	Examination Report for European Patent Application No. 01 973 651.1-1528, dated March 22, 2004, 3 pages.	
	C180	Examination Report for European Patent Application No. 01 973 651.1-1528, dated November 12, 2004, 9 pages.	

Examiner Signature		Date Considered	
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>				Application Number	10/603,852
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				Art Unit	2811
				Examiner Name	D. W. Owens
Sheet	2	of	2	Attorney Docket Number	ASC-022CPC1

	C181	Examination Report for European Patent Application No. 01 989 893.1-1235, dated August 16, 2004, 5 pages.	
	C182	Examination Report for European Patent Application No. 02 709 406.9-2203, dated March 24, 2005, 5 pages.	
	C183	Examination Report for European Patent Application No. 02 709 406.9-2203, dated May 11, 2004, 3 pages.	
	C184	Examination Report for European Patent Application No. 98 931 529.6-2203, dated January 10, 2002, 4 pages.	
	C185	Examination Report for European Patent Application No. 98 931 529.6-2203, dated May 9, 2003, 5 pages.	
	C186	Fitzgerald et al., "Dislocations in Relaxed SiGe/Si Heterostructures," Physica Status Solidi A, Applied Research, Vol. 171, Nr. 1, pg. 227-238 (1999).	
	C187	International Search Report for Int'l Application No. PCT/US01/46322, mailed Jan 22, 2003.	
	C188	International Search Report for Patent Application No. PCT/US 98/13076, dated October 27, 1998, 2 pages.	
	C189	International Search Report for Related International Application No. PCT/US2003/18007, January 5, 2004.	
	C190	Klauk et al., "Thermal stability of undoped strained Si channel SiGe heterostructures," American Institute of Physics, April 1, 1996, pgs. 1975-1977.	
	C191	Notice of Final Rejection for Korean Patent Application No. 10-1999-7012279, dated February 25, 2003 2 pages (English translation attached).	
	C192	Notice of Preliminary Rejection for Korean Patent Application No. 10-1999-7012279, dated February 21, 2002, 2 pages (English translation attached).	
	C193	Partial International Search Report for International Patent Application No. PCT/US2006/035814, February 7, 2007 (7 pages).	
	C194	Rosenblad et al., "Strain relaxation of graded SiGe buffers grown at very high rates," Mat. Sci. and Engineering B, Vol. 71, Nr. 1-3, pg. 20-23 (2000).	
	C195	Soderbarg, "Fabrication of BESOI-Materials Using Implanted Nitrogen as an Effective Etch Stop Barrier," 1989 IEEE SOS/SOI Technology Conference, pp. 64.	
	C196	Thean et al., "Performance of super-critical strained-si directly on insulator (SC-SSOI) CMOS based on high-performance PD-SOI technology," 2005 Symp. on VLSI Tech., Dig. Tech. Papers, pp. 134-135.	

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